Analog Behavior in Custom IC Variation-Aware Design (Invited Special Session Paper)

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Tails Statistical tails!

By definition, statistical tails are improbable.

Challenges:

- Infeasible to simulate 1G samples
- Let alone optimize at 1G-tails



Due to Market Pressure (and History), Transistors Are Shrinking...



[ITRS, 2011]

Transistors are shrinking But atoms aren't!



traditional



sub 10 nm (2020)

A. Asenov, "Statistical Nano CMOS Variability and Its Impact on SRAM", Chapter 3, A. Singhee and R. Rutenbar, Eds., Extreme Statistics in Nanoscale Memory Design, Springer, 2010

Variation = atoms out of place ...Propagating from devices to performance & yield



Modern Process Nodes Have High Variation ... and It's Getting Worse Example: GF 40-nm vs. 28-nm on Single Device



and for global+mismatch combined; for both nmos and pmos. [Yao et al, DAC 2012]

Applicability of FF/SS Corners? Example on GF 28-nm, PLL VCO, Avg. Duty Cycle



Why: FF/SS were designed to bracket performance at the device *level*, for (digital) speed and power outputs.

Therefore not well-suited to analog / RF circuits.

Variation-Handling Flow: PVT (Where the "P" is FF/SS corners)



Pros: familiarity, speed, scalability

Cons: {ignores local variation, poor model of global} \rightarrow hurts yield, performance



Variation-Handling Flow: Direct MC



Cons: way too many sims

Idea: Use corners. Just make the corners good. This is the sigma-driven corners flow.



 3σ Yield == Yield of 99.73% (not 3 standard deviations)

Tool support for a sigma-driven corners flow



On "Analog"

- Analog =
 - Continuous in time, or
 - Continuous in value (voltage, current)
- Q: Where do we need to do analog analysis?

(i.e. analyze continuous in time, or value)

- A:
 - Traditional "analog" circuits (opamps, bias generators, ..)
 - Mixed analog-digital circuits (ADCs, ..)
 - Bitcells, sense amps
 - Especially when variation is present!
 - Standard cells
 - Especially when variation is present!
- Another Q that currently has the same A: where do we need to run SPICE-based analysis?



Challenges in Memory & Standard Cells

- Plain Monte Carlo is too expensive
 - Failure rate is $\approx 1/1M$ to $\approx 1/1G$. Tails!
 - Running 10M to 10G+ MC samples is infeasible
- Automated sizing is common industrial practice
 - E.g. optimize a library of standard cells

• How to reconcile these in the sigma-driven corners flow?

Sigma-driven corners flow: Variant for memory & standard cells



Tool support for a sigma-driven corners flow For high- σ memory and standard cells



Make this great

e.g. High-Sigma Monte Carlo (100x+ faster than plain MC)

Make this great e.g. optimization tool (fast SPICE-accurate global optimization)

Make this great

e.g. High-Sigma Monte Carlo (100x+ faster than plain MC)





High-Sigma Monte Carlo Algorithm Exploits scalability of Monte Carlo

- 1. Generate (but don't simulate) 5G Monte Carlo samples
- 2. Order the 5G samples:
 - Choose initial samples, & simulate
 - Build model that predicts order
 - Order the samples using model
- 3. Simulate in that order
 - Until tail found / all failures found

offset

High-Sigma Monte Carlo Algorithm **Details**



- Generate (but don't simulate) 1B Monte Carlo samples.
- Choose initial samples = the 1000 generated samples that are farthest from nominal.
- Simulate initial samples.

 Build model that predicts order, mapping process points → simulated output values.

 Order the samples using model.
Simulate the points in order, until all failures found or max # sims hit.

Cell Optimizer Algorithm Truly global. Data-mines simulations to the max.



Example: minimize 5σ flip flop setup time Using High-Sigma Monte Carlo (HSMC) and Cell Optimizer



Sigma-driven flow for memory and standard cells: Industrial user success stories

- Efficiently optimizing a bitcell design for optimal read margin and write margin simultaneously, using a different testbench for each measurement. This is for both nominal and high-sigma variation conditions. 20nm, 16nm.
- Tuning, porting, retargeting, and migrating large standard cell libraries, to support a large designer base. This task is extremely time consuming and expensive to do manually. Furthermore, these cells need to be optimized to work well under high-sigma conditions. 28nm, 20nm, 16nm.
- In a large library of standard cells, while all of the cells perform well under nominal conditions, identifying which cells fail under high-sigma conditions and automatically fixing them via resizing.

Sigma-Driven Corners: A Unified Flow For 3- σ , High- σ , and even PVT Variation



Conclusion

- Variation is a huge problem.
- Analog analysis includes memory and standard cells
- The sigma-driven corners flow is a unified way to handle variation. Fast, effective, familiar.
- For memory and standard cells, the most effective variant has:
 - Fast high-sigma analysis. E.g. High-Sigma Monte Carlo.
 - Fast global optimization. E.g. Cell Optimizer.



More detail:

T. McConaghy, K. Breen, J. Dyck, and A. Gupta. Variation-Aware Design of Custom Integrated Circuits: A Hands-on Field Guide. Springer, 2012.

Extra slides



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HSMC on Bitcell cell_i, w/ 100M MC samples Shows: Fast, Accurate, Scalable



HSMC Convergence Curve on Bitcell cell_i Shows: Verifiable ("How can I trust it?")



Cell Optimizer: Example Step 1 Initial sampling, simulate, build model, Choose xnew



Cell Optimizer: Example Step 2 Simulate new point, update model, choose xnew

